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(54) INTEGRATED CIRCUIT WITH BORDERLESS CONTACTS

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(US)

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(52)	U.S. Cl.
(58)	Field of Search 438/664, 666,
, ,	438/683 674 704 740 970 634 675

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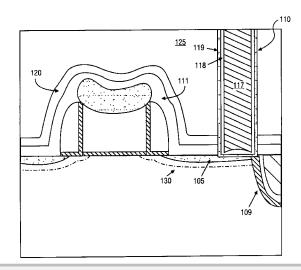
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(57) ABSTRACT

An integrated circuit comprising a conductive region formed on a semiconductor substrate, a silicate glass layer formed on the conductive region, and an etch stop layer formed on the silicate glass layer. The integrated circuit also includes a borderless contact that is coupled to the conductive region.

10 Claims, 3 Drawing Sheets





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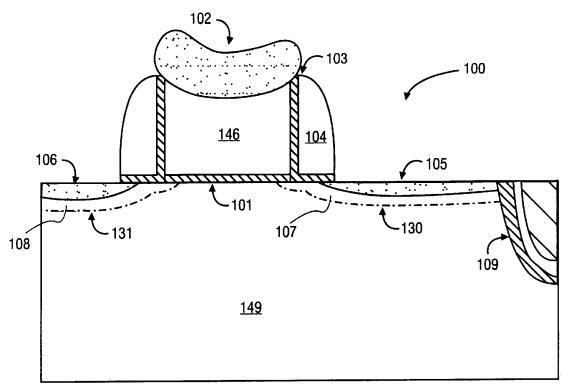


FIGURE 1

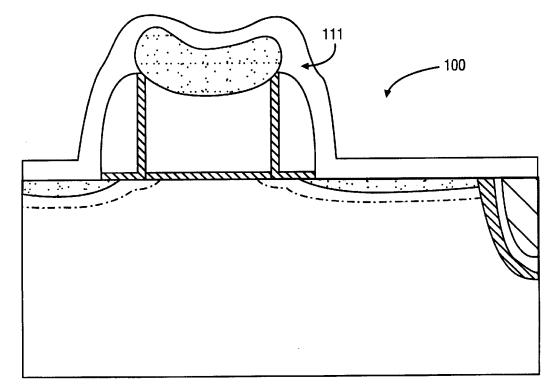


FIGURE 2



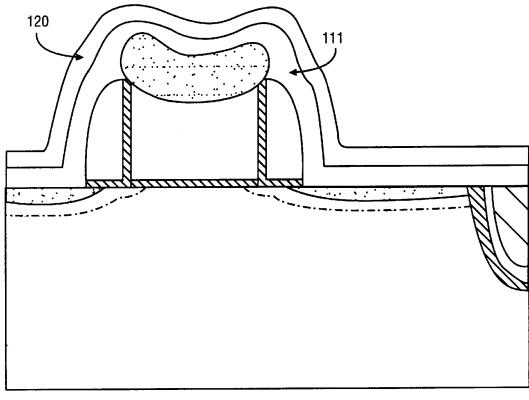


FIGURE 3

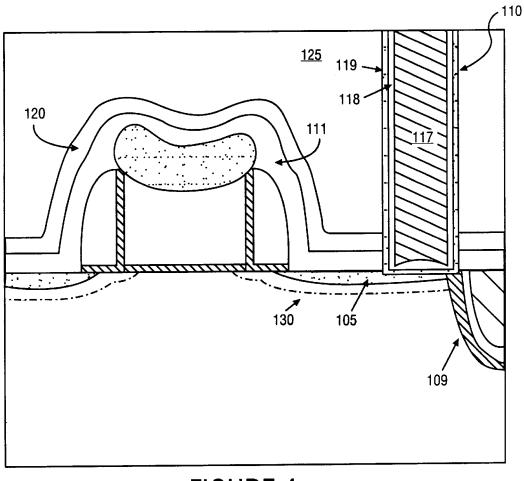


FIGURE 4

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